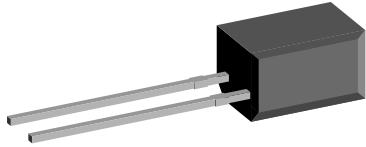


Silicon PIN Photodiode, RoHS Compliant



94 8480

FEATURES

- Package type: leaded
- Package form: side view
- Dimensions (in mm): 5 x 4 x 6.8
- Radiant sensitive area (in mm²): 7.5
- High radiant sensitivity
- Daylight blocking filter matched with 940 nm emitters
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 65^\circ$
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

DESCRIPTION

BPW41N is a PIN photodiode with high speed and high radiant sensitivity in a black, side view plastic package with daylight blocking filter. Filter bandwidth is matched with 900 nm to 950 nm IR emitters.

APPLICATIONS

- High speed detector for infrared radiation
- Infrared remote control and free air data transmission systems, e.g. in combination with TSALxxxx series IR emitters

PRODUCT SUMMARY			
COMPONENT	I_{ra} (μA)	φ (deg)	$\lambda_{0.5}$ (nm)
BPW41N	45	± 65	870 to 1050

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPW41N	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	Side view

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	60	V
Power dissipation	$T_{amb} \leq 25^\circ C$	P_V	215	mW
Junction temperature		T_j	100	$^\circ C$
Operating temperature range		T_{amb}	- 40 to + 100	$^\circ C$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s	T_{sd}	260	$^\circ C$
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R_{thJA}	350	K/W

Note

$T_{amb} = 25^\circ C$, unless otherwise specified



BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Breakdown voltage	$I_R = 100 \mu A, E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 10 V, E = 0$	I_{ro}		2	30	nA
Diode capacitance	$V_R = 0 V, f = 1 \text{ MHz}, E = 0$	C_D		70		pF
	$V_R = 3 V, f = 1 \text{ MHz}, E = 0$	C_D		25	40	pF
Open circuit Voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	V_o		350		mV
Temperature coefficient of V_o	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK_{V_o}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	I_k		38		μA
Temperature coefficient of I_k	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK_{I_k}		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_R = 5 V$	I_{ra}	43	45		μA
Angle of half sensitivity		φ		± 65		deg
Wavelength of peak sensitivity		λ_p		950		nm
Range of spectral bandwidth		$\lambda_{0.5}$		870 to 1050		nm
Noise equivalent power	$V_R = 10 V, \lambda = 950 \text{ nm}$	NEP		4×10^{-14}		W/ $\sqrt{\text{Hz}}$
Rise time	$V_R = 10 V, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t_r		100		ns
Fall time	$V_R = 10 V, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t_f		100		ns

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

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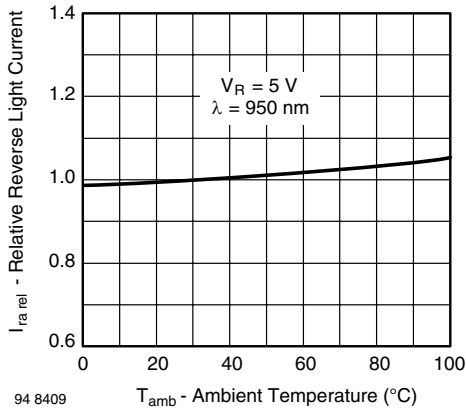


Fig. 1 - Relative Reverse Light Current vs. Ambient Temperature

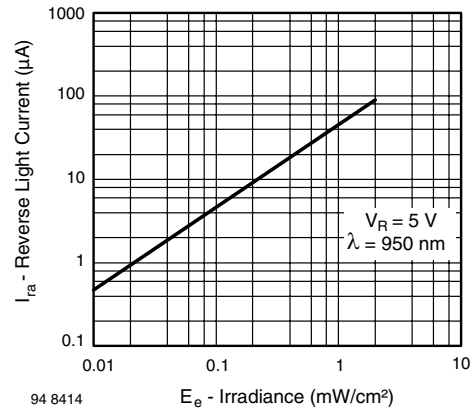


Fig. 2 - Reverse Light Current vs. Irradiance

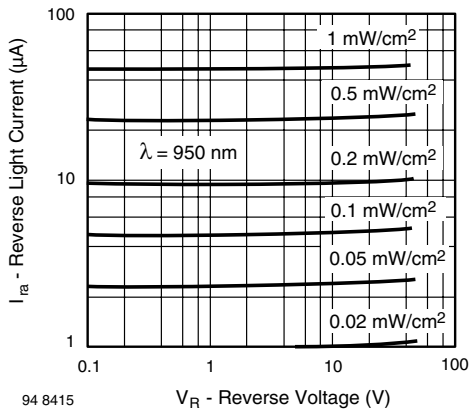


Fig. 3 - Reverse Light Current vs. Reverse Voltage

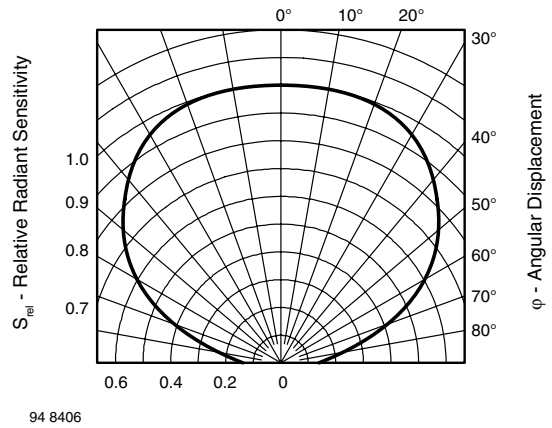


Fig. 6 - Relative Radiant Sensitivity vs. Angular Displacement

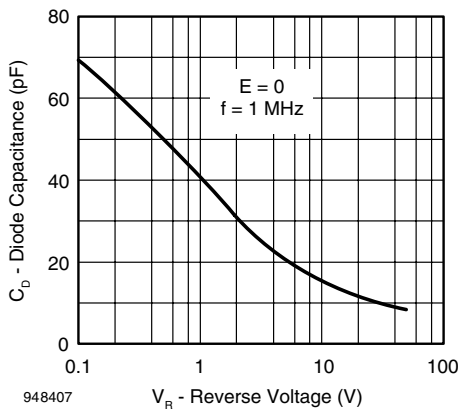


Fig. 4 - Diode Capacitance vs. Reverse Voltage

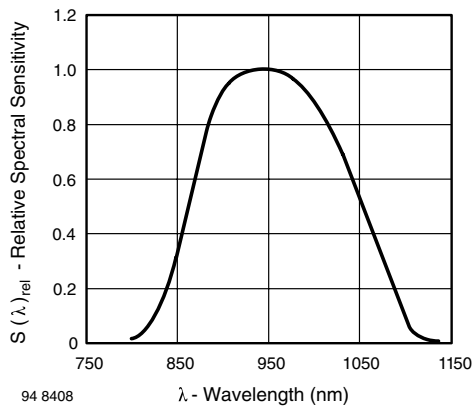
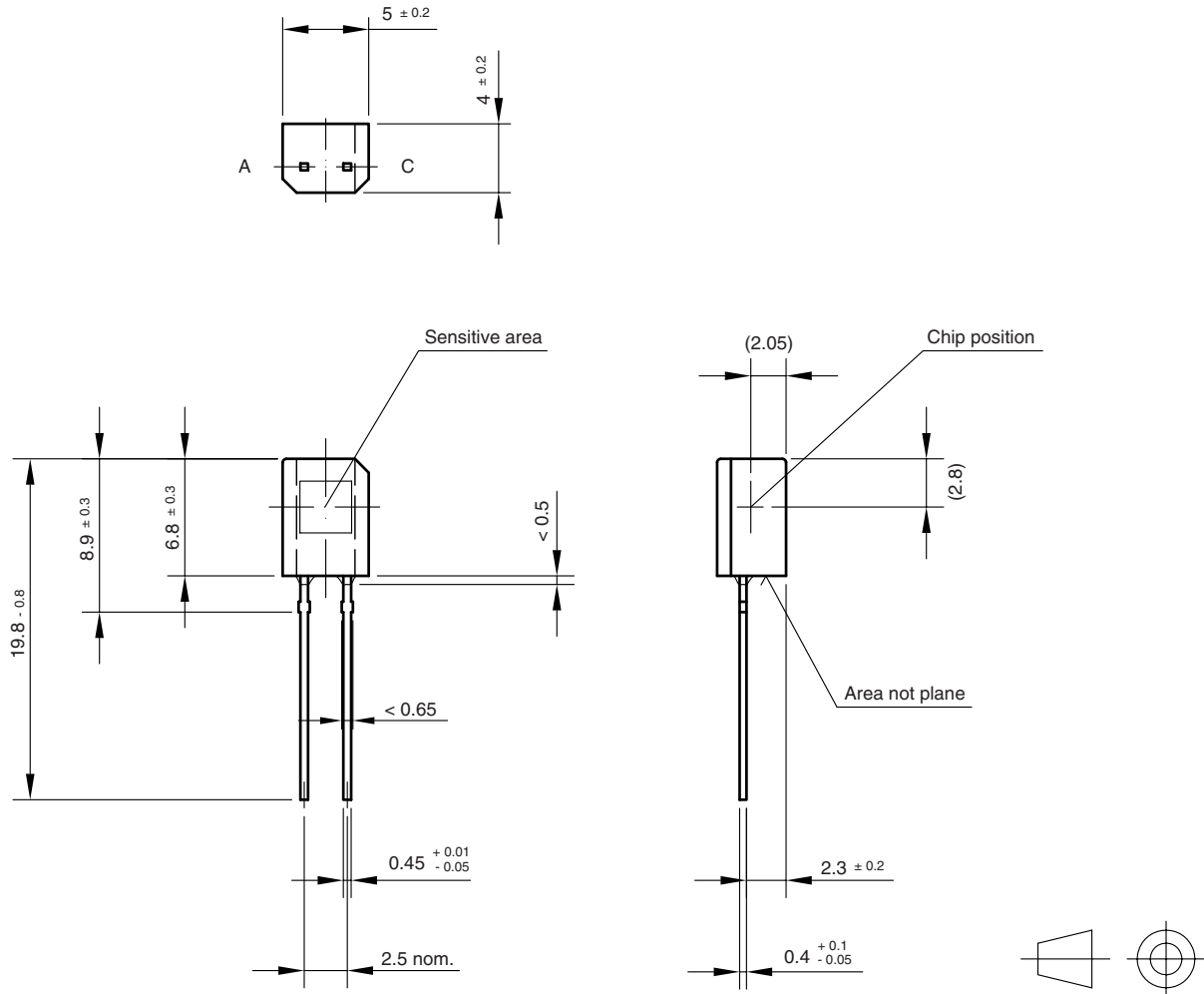


Fig. 5 - Relative Spectral Sensitivity vs. Wavelength



PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5108.01-4
Issue:1; 01.07.96
96 12195

technical drawings
according to DIN
specifications



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